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Silicon Bidirectional Thyristors

Designed for high performance full—wave ac control applications where high noise immunity and commutating di/dt are required.

Features

- Blocking Voltage to 800 Volts
- On-State Current Rating of 12 Amperes RMS at 70°C
- Uniform Gate Trigger Currents in Three Quadrants, Q1, Q2, and Q3
- High Immunity to dv/dt 250 V/µs Minimum at 125°C
- High Commutating di/dt 6.5 A/ms Minimum at 125°C
- Industry Standard TO-220 Package
- High Surge Current Capability 100 Amperes
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---|---------------------------------------|-------------------|--------------------|
| Peak Repetitive Off–State Voltage (Note 1) (T _J = -40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open) | V _{DRM,} V _{RRM} | | V |
| MAC12D MAC12M MAC12N | | 400 600 800 | |
| On-State RMS Current (All Conduction Angles; T _C = 70°C) | I _{T(RMS)} | 12 | Α |
| Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, T _J = 125°C) | I _{TSM} | 100 | Α |
| Circuit Fusing Consideration (t = 8.33 ms) | I ² t | 41 | A ² sec |
| Peak Gate Power (Pulse Width \leq 1.0 μ s, T _C = 80°C) | P _{GM} | 16 | W |
| Average Gate Power $(t = 8.3 \text{ ms}, T_C = 80^{\circ}\text{C})$ | P _{G(AV)} | 0.35 | W |
| Operating Junction Temperature Range | TJ | -40 to +125 | °C |
| Storage Temperature Range | T _{stg} | -40 to +150 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



Littelfuse.com

TRIACS 12 AMPERES RMS 400 thru 800 VOLTS





MARKING DIAGRAM



TO-220 CASE 221A STYLE 4

x = D, M, or N
A = Assembly Location
Y = Year
WW = Work Week

= Pb-Free Package

| PIN ASSIGNMENT | | | |
|----------------|-----------------|--|--|
| 1 | Main Terminal 1 | | |
| 2 | Main Terminal 2 | | |
| 3 | Gate | | |
| 4 | Main Terminal 2 | | |

ORDERING INFORMATION

| Device | Package | Shipping |
|---------|---------------------|-----------------|
| MAC12DG | TO-220 | 50 Units / Rail |
| | (Pb-Free) | |
| MAC12MG | TO-220 (Pb-Free) | 50 Units / Rail |
| MAC12NG | TO-220 (Pb-Free) | 50 Units / Rail |

THERMAL CHARACTERISTICS

| Characteristic | | Symbol | Value | Unit |
|------------------------|---|---------------|-------------|------|
| Thermal Resistance, | Junction-to-Case Junction-to-Ambient | $R_{	hetaJC}$ | 2.2 62.5 | °C/W |
| Maximum Lead Temperatu | re for Soldering Purposes 1/8" from Case for 10 Seconds | TL | 260 | °C |

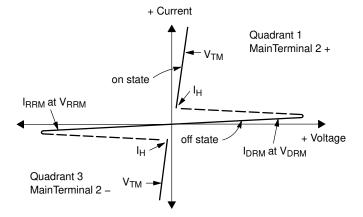
| Characteristic Sy | | | Min | Тур | Max | Unit |
|---|---|--|-------------------|----------------------|-------------------|------|
| OFF CHARACTERISTICS | | | | | | |
| Peak Repetitive Blocking Current $(V_D = Rated V_{DRM}, V_{RRM}, Gate Open)$ | T _J = 25°C T _J = 125°C | I _{DRM} , I _{RRM} | _ _ | _ _ | 0.01 2.0 | mA |
| ON CHARACTERISTICS | | | | | | |
| Peak On–State Voltage (Note 2) (I _{TM} = ±17 A) | | V_{TM} | _ | - | 1.85 | V |
| Gate Trigger Current (Continuous dc) (V_D = 12 V, R_L = 100 Ω) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) | | I _{GT} | 5.0 5.0 5.0 | 13 13 13 | 35 35 35 | mA |
| Hold Current (V _D = 12 V, Gate Open, Initiating Current = ±150 mA) | | I _H | - | 20 | 40 | mA |
| Latch Current (V_D = 24 V, I_G = 35 mA) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) | | IL | - - - | 20 30 20 | 50 80 50 | mA |
| Gate Trigger Voltage (Continuous dc) (V_D = 12 V, R_L = 100 Ω) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) | | V _{GT} | 0.5 0.5 0.5 | 0.78 0.70 0.71 | 1.5 1.5 1.5 | V |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Rate of Change of Commutating Current $(V_D=400\ V,\ ITM=4.4A,\ Commutating\ dv/dt=18\ V/\mu s,\ Gate\ Open\ T_J=125^{\circ}C,\ f=250\ Hz,\ No\ Snubber)$ | , | (di/dt)c | 6.5 | - | - | A/ms |
| Critical Rate of Rise of Off–State Voltage (V _D = Rated V _{DRM} , Exponential Waveform, Gate Open, T _J = 125°C | ;) | dv/dt | 250 | 500 | - | V/μs |
| Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 μsec; diG/dt = 200 mA/μsec; f = 60 Hz | di/dt | - | - | 10 | A/μs | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

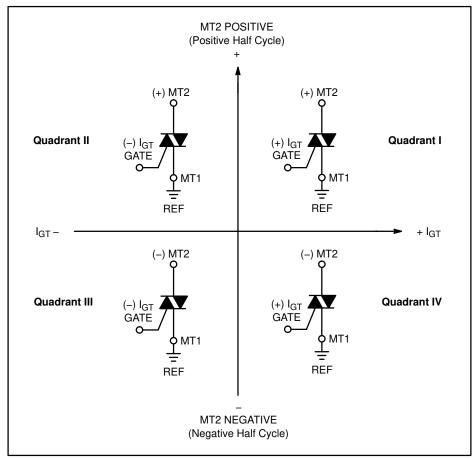
2. Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

Voltage Current Characteristic of Triacs (Bidirectional Device)

| Symbol | Parameter |
|------------------|---|
| V _{DRM} | Peak Repetitive Forward Off State Voltage |
| I _{DRM} | Peak Forward Blocking Current |
| V _{RRM} | Peak Repetitive Reverse Off State Voltage |
| I _{RRM} | Peak Reverse Blocking Current |
| V _{TM} | Maximum On State Voltage |
| I _H | Holding Current |



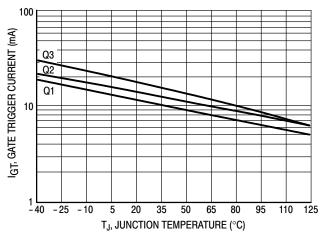
Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

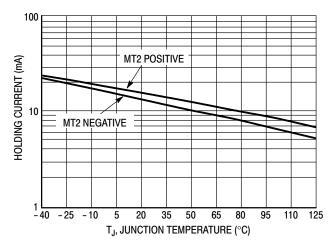
1.10



V_{GT}, GATE TRIGGER VOLTAGE (VOLT) 1.00 0.90 Q2 0.80 0.70 0.60 0.50 -25 -10 40 20 35 50 65 80 95 110 125 T_J, JUNCTION TEMPERATURE (°C)

Figure 1. Typical Gate Trigger Current versus Junction Temperature

Figure 2. Typical Gate Trigger Voltage versus Junction Temperature



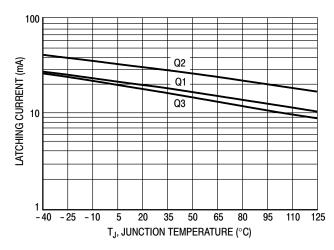
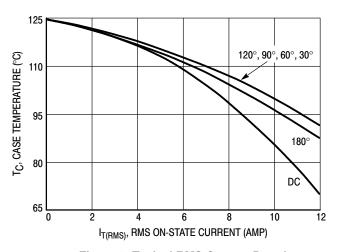


Figure 3. Typical Holding Current versus Junction Temperature

Figure 4. Typical Latching Current versus Junction Temperature



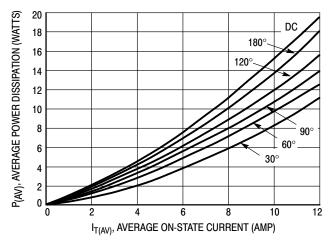


Figure 5. Typical RMS Current Derating

Figure 6. On-State Power Dissipation

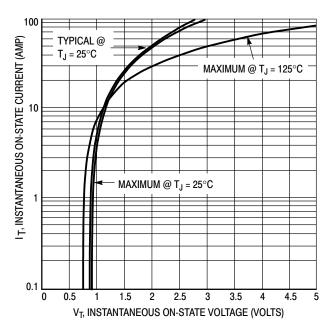


Figure 7. Typical On-State Characteristics

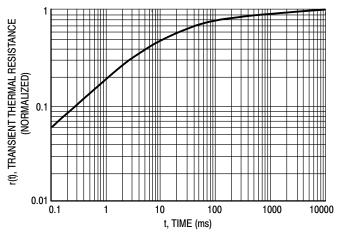
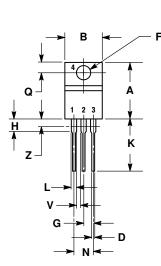
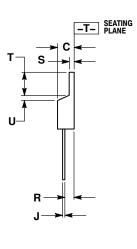


Figure 8. Typical Thermal Response

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH**





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH. DIMENSION Z DEFINES A ZONE WHERE ALL
- BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.570 | 0.620 | 14.48 | 15.75 |
| В | 0.380 | 0.415 | 9.66 | 10.53 |
| С | 0.160 | 0.190 | 4.07 | 4.83 |
| D | 0.025 | 0.038 | 0.64 | 0.96 |
| F | 0.142 | 0.161 | 3.61 | 4.09 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| Н | 0.110 | 0.161 | 2.80 | 4.10 |
| J | 0.014 | 0.024 | 0.36 | 0.61 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| ٧ | 0.045 | | 1.15 | |
| Z | | 0.080 | | 2.04 |

STYLE 4:

- PIN 1. MAIN TERMINAL 1
 - MAIN TERMINAL 2 GATE

 - MAIN TERMINAL 2

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